

**Silicon PNP Power Transistors****2SA1133 2SA1133A****DESCRIPTION**

- With TO-220 package
- High breakdown voltage
- High power dissipation
- Complement to type 2SC2660/2660A

APPLICATIONS

- For power amplifier and TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base

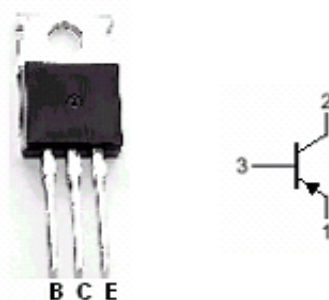


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CB0}	Collector-base voltage		Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	2SA1133	Open base	-150	V
		2SA1133A		-180	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-2.0	A
I_{CM}	Collector current-peak			-3.0	A
P_T	Total power dissipation		$T_C=25^\circ\text{C}$	30	W
T_J	Junction temperature			150	$^\circ\text{C}$
T_{stg}	Storage temperature			-55~150	$^\circ\text{C}$

**Silicon PNP Power Transistors****2SA1133 2SA1133A****CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA1133	I _C =-5mA, I _B =0	-150			V
		2SA1133A		-180			
V _{(BR)CBO}	Collector-base breakdown voltage		I _C =-0.5mA, I _E =0	-200			V
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-0.5mA, I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =-500mA; I _B =-50mA			-1.0	V
V _{BE}	Base-emitter on voltage		I _C =-400mA; V _{CE} =-10V			-1.0	V
I _{CBO}	Collector cut-off current		V _{CB} =-200V; I _E =0			-50	μA
I _{EBO}	Emitter cut-off current		V _{EB} =-4V; I _C =0			-50	μA
h _{FE1}	DC current gain		I _C =-150mA; V _{CE} =-10V	60		240	
h _{FE2}	DC current gain		I _C =-400mA; V _{CE} =-10V	50			

◆ **h_{FE1} Classifications**

Q	P
60-140	100-240



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PACKAGE OUTLINE

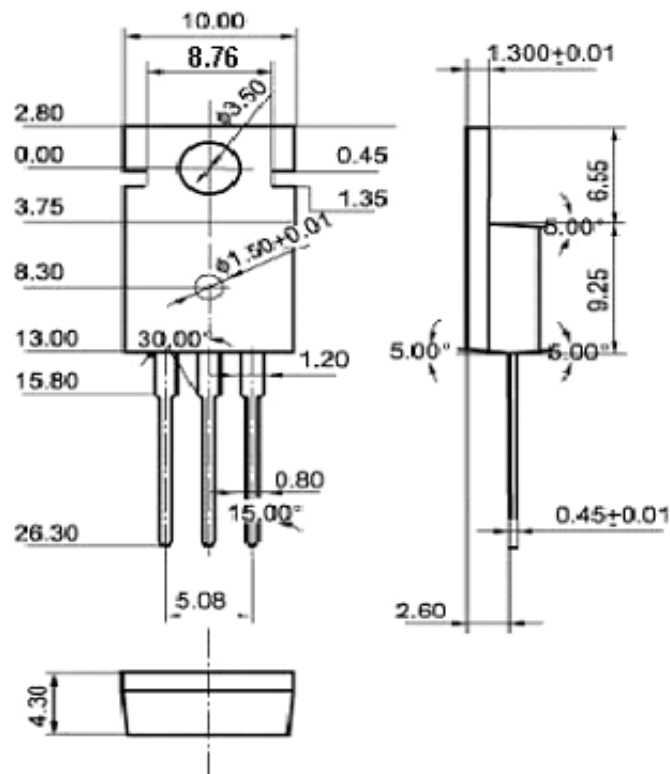


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)